Low-Voltage CMOS Quad 2-Input Multiplexer

With 5.0 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX257 is a high performance, quad 2–input multiplexer with 3–state outputs operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX257 inputs to be safely driven from 5.0 V devices.

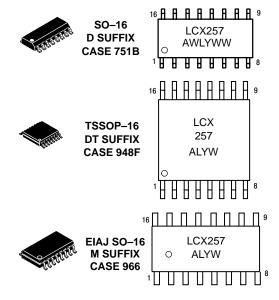
Four bits of data from two sources can be selected using the Select input. The four outputs present the selected data in the true (non–inverted) form. The outputs may be switched to a high impedance state by placing a logic HIGH on the Output Enable (\overline{OE}) input. Current drive capability is 24 mA at the outputs.

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5.0 V Tolerant Interface Capability with 5.0 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 V$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V



http://onsemi.com

MARKING DIAGRAMS



A = Assembly Location

L, WL = Wafer Lot
Y = Year
W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74LCX257D	SO-16	48 Units/Rail
MC74LCX257DR2	SO-16	2500 Units/Reel
MC74LCX257DT	TSSOP-16	96 Units/Rail
MC74LCX257DTR	TSSOP-16	2500 Units/Reel
MC74LCX158DTR2	TSSOP-16	2500 Units/Reel
MC74LCX257M	EIAJ SO-16	48 Units/Rail
MC74LCX257MEL	EIAJ SO-16	2000 Units/Reel

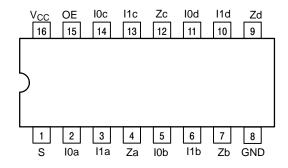


Figure 1. Pinout: 16-Lead Plastic Package (Top View)

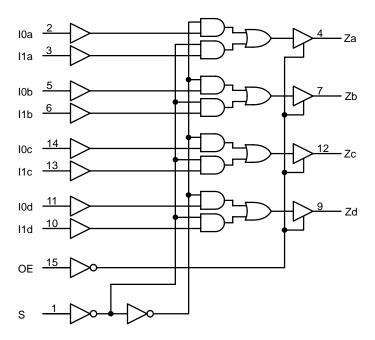


Figure 2. Logic Diagram

PIN NAMES

Pins	Function		
I0n	Source 0 Data Inputs		
l1n	Source 1 Data Inputs		
ŌĒ	Output Enable Input		
S	Select Input		
Zn	Outputs		

TRUTH TABLE

	Inp	Outputs		
ŌĒ	S	l0n	l1n	Zn
Н	Х	Х	Х	Z
L	Н	Х	L	L
L	Н	Х	н	Н
L	L	L	Х	L
L	L	Н	Х	Н

H = High Voltage Level

Low Voltage Level

X = High or Low Voltage Level and Transitions are Acceptable
 Z = High Impedance State

For ICC reasons, DO NOT FLOAT Inputs

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_1 \le +7.0$	Output in 3–State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1.)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
lok	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
I _O	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

^{*}Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Paramete	r	Min	Туре	Max	Unit
V _{CC}	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
Vo	Output Voltage	(HIGH or LOW State) (3–State)	0		V _{CC} 5.5	V
I _{OH}	HIGH Level Output Current	$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			-24 -12 -8	mA
I _{OL}	LOW Level Output Current	$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			+24 +12 +8	mA
T _A	Operating Free–Air Temperature		-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, V_{CC} = 3.0 V		0		10	ns/V

^{1.} I_O absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS

			T _A = −40°C			
Symbol	Characteristic	Condition	Min	Max	Unit	
V _{IH}	HIGH Level Input Voltage (Note 2.)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V	
		2.7 V ≤ V _{CC} ≤ 3.6 V	2.0			
V _{IL}	LOW Level Input Voltage (Note 2.)	2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	V	
		2.7 V ≤ V _{CC} ≤ 3.6 V		0.8		
V _{OH}	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OH} = -100 \mu\text{A}$	V _{CC} - 0.2		V	
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.8			
		V _{CC} = 2.7 V; I _{OH} = -12 mA	2.2			
		V _{CC} = 3.0 V; I _{OH} = -18 mA	2.4			
		V _{CC} = 3.0 V; I _{OH} = -24 mA	2.2			
V _{OL}	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V	
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.6		
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4		
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4		
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55		
I _I	Input Leakage Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5	μΑ	
I _{OZ}	3-State Output Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le V_{O} \le 5.5 \text{ V};$ $V_{I} = V_{IH} \text{ or } V_{IL}$		±5	μА	
I _{OFF}	Power-Off Leakage Current	$V_{CC} = 0 \text{ V}; V_{I} \text{ or } V_{O} = 5.5 \text{ V}$		10	μΑ	
I _{CC}	Quiescent Supply Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$		10	μΑ	
		$2.3 \le V_{CC} \le 3.6 \text{ V}; 3.6 \le V_{I} \text{ or } V_{O} \le 5.5 \text{ V}$		±10		
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ	

^{2.} These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS $t_R=t_F$ = 2.5 ns; R_L = 500 Ω

					Lin	nits			
				$T_A = -40^{\circ}C$ to $+85^{\circ}C$					
			V _{CC} = 3.3	3 V ± 0.3 V	V _{CC} =	2.7 V	V _{CC} = 2.5	$V \pm 0.2 V$	
			C _L =	50 pF	C _L =	50 pF	C _L =	30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
t _{PLH}	Propagation Delay	1	1.5	6.0	1.5	6.5	1.5	7.2	ns
t _{PHL}	In to Zn		1.5	6.0	1.5	6.5	1.5	7.2	
t _{PLH}	Propagation Delay	1, 2	1.5	7.0	1.5	8.5	1.5	9.1	ns
t _{PHL}	S to Zn		1.5	7.0	1.5	8.5	1.5	9.1	
t _{PZH}	Output Enable Time to	3	1.5	7.0	1.5	8.5	1.5	9.1	ns
t _{PZL}	High and Low Level		1.5	7.0	1.5	8.5	1.5	9.1	
t _{PHZ}	Output Disable Time From	3	1.5	5.5	1.5	6.0	1.5	6.6	ns
t _{PLZ}	High and Low Level		1.5	5.5	1.5	6.0	1.5	6.6	
toshL	Output-to-Output Skew			1.0					ns
toslh	(Note 3.)			1.0					

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

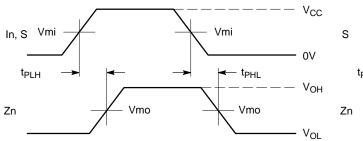
DYNAMIC SWITCHING CHARACTERISTICS

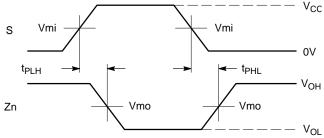
			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V
	(Note 4.)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		0.6		V
V _{OLV}	Dynamic LOW Valley Voltage	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		-0.8		V
	(Note 4.)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		-0.6		V

^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	7	pF
C _{I/O}	Input/Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF



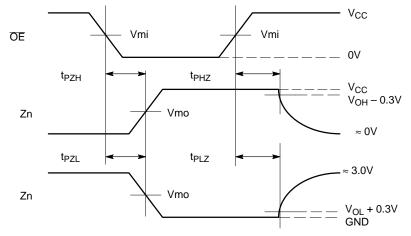


WAVEFORM 1 - NON-INVERTING PROPAGATION DELAYS

 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1.0 \text{ MHz}; t_W = 500 \text{ ns}$

WAVEFORM 2 – INVERTING PROPAGATION DELAYS

 t_R = t_F = 2.5 ns, 10% to 90%; f = 1.0 MHz; t_W = 500 ns



WAVEFORM 3 - OUTPUT ENABLE AND DISABLE TIMES

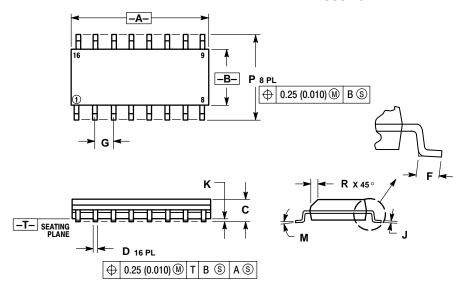
 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1.0 \text{ MHz}; t_W = 500 \text{ ns}$

	Vcc					
Symbol	3.3 V <u>+</u> 0.3 V	2.7 V	2.5 V <u>+</u> 0.2 V			
Vmi	1.5 V	1.5 V	Vcc/2			
Vmo	1.5 V	1.5 V	Vcc/2			
V _{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V			
V _{LZ}	V _{OH} – 0.3 V	V _{OH} – 0.3 V	V _{OH} – 0.15 V			

Figure 3. AC Waveforms

PACKAGE DIMENSIONS

SO-16 **D SUFFIX** CASE 751B-05 **ISSUE J**

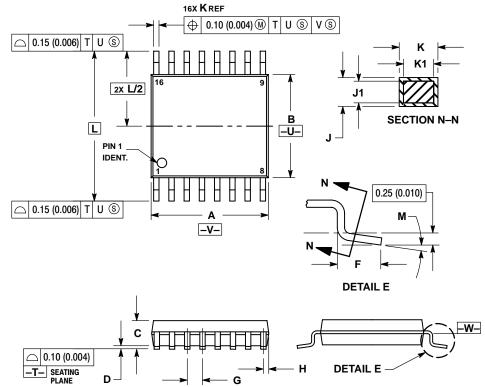


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M. 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PEH SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE O**



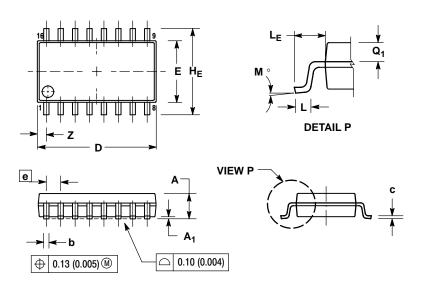
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982..
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH.
 PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED
- PHOI HUSION SHALL NOT EXCEED
 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM
 MATERIAL CONDITION.
 TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	-				
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
M	0°	8°	0°	8°	

PACKAGE DIMENSIONS

SOIC EIAJ-16 M SUFFIX CASE 966-01 **ISSUE O**



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE, MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
- PER SIDE. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018)

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Ε	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		0.78		0.031

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